

TOSHIBA PHOTOCOUPLER GaAs IRED & PHOTO-TRANSISTOR

TLP631, TLP632

PROGRAMMABLE CONTROLLERS

AC/DC-INPUT MODULE

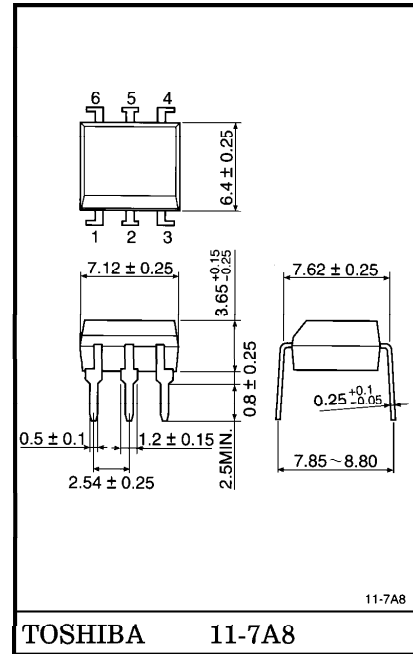
SOLID STATE RELAY

The TOSHIBA TLP631 and TLP632 consist of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode in a six lead plastic DIP.

TLP632 is no-base internal connection for high-EMI environments.

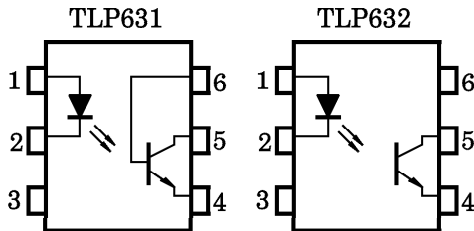
- Collector-Emitter Voltage : 55V (MIN.)
- Current Transfer Ratio : 50% (MIN.)
Rank GB : 100% (MIN.)
- Isolation Voltage : 5000V_{rms} (MIN.)
- UL Recognized : UL1577, File No. E67349

Unit in mm



Weight : 0.4g

PIN CONFIGURATIONS (TOP VIEW)



- | | |
|---------------|---------------|
| 1 : ANODE | 1 : ANODE |
| 2 : CATHODE | 2 : CATHODE |
| 3 : N.C. | 3 : N.C. |
| 4 : EMITTER | 4 : EMITTER |
| 5 : COLLECTOR | 5 : COLLECTOR |
| 6 : BASE | 6 : N.C. |

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- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with domestic garbage.
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MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current	I _F	60	mA
	Forward Current Derating (Ta ≥ 39°C)	ΔI _F /°C	-0.7	mA/°C
	Peak Forward Current (100μs pulse, 100pps)	I _{FP}	1	A
	Reverse Voltage	V _R	5	V
	Junction Temperature	T _j	125	°C
DETECTOR	Collector-Emitter Voltage	V _{CEO}	55	V
	Collector-Base Voltage (TLP631)	V _{CB0}	80	V
	Emitter-Collector Voltage	V _{ECO}	7	V
	Emitter-Base Voltage (TLP631)	V _{EBO}	7	V
	Collector Current	I _C	50	mA
	Power Dissipation	P _C	150	mW
	Power Dissipation Derating (Ta ≥ 25°C)	ΔP _C /°C	-1.5	mW/°C
	Junction Temperature	T _j	125	°C
Storage Temperature Range		T _{stg}	-55~125	°C
Operating Temperature Range		T _{opr}	-55~100	°C
Lead Soldering Temperature (10s)		T _{sol}	260	°C
Total Package Power Dissipation		P _T	250	mW
Total Package Power Dissipation Derating (Ta ≥ 25°C)		ΔP _T /°C	-2.5	mW/°C
Isolation Voltage (AC, 1 min., R.H. ≤ 60%)		BV _S	5000	V _{rms}

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V _{CC}	—	5	24	V
Forward Current	I _F	—	16	25	mA
Collector Current	I _C	—	1	10	mA
Operating Temperature	T _{opr}	-25	—	85	°C

INDIVIDUAL ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V_F	$I_F = 10\text{mA}$	1.0	1.15	1.3	V
	Reverse Current	I_R	$V_R = 5\text{V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1\text{MHz}$	—	30	—	pF
DETECTOR	Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 0.5\text{mA}$	55	—	—	V
	Emitter-Collector Breakdown Voltage	$V_{(BR)ECO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector-Base Breakdown Voltage (TLP631)	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}$	80	—	—	V
	Emitter-Base Breakdown Voltage (TLP631)	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}$	7	—	—	V
	Collector Dark Current	I_{CEO}	$V_{CE} = 24\text{V}$	—	10	100	nA
			$V_{CE} = 24\text{V}, T_a = 85^\circ\text{C}$	—	2	50	μA
Capacitance Collector to Emitter	C_{CE}	$V = 0, f = 1\text{MHz}$	—	10	—	pF	

COUPLED ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Current Transfer Ratio	I_C / I_F	$I_F = 5\text{mA}, V_{CE} = 5\text{V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1\text{mA}, V_{CE} = 0.4\text{V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-Emitter Saturation Voltage	$V_{CE} (\text{sat})$	$I_C = 2.4\text{mA}, I_F = 8\text{mA}$	—	—	0.4	V

ISOLATION CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Capacitance (Input to Output)	C _S	V _S = 0, f = 1MHz	—	0.8	—	pF
Isolation Resistance	R _S	V _S = 500V, R.H. ≤ 60%	5 × 10 ¹⁰	10 ¹⁴	—	Ω
Isolation Voltage	BV _S	AC, 1 minute	5000	—	—	V _{rms}
		AC, 1 second, in oil	—	10000	—	
		DC, 1 minute, in oil	—	10000	—	V _{dc}

SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Rise Time	t _r	V _{CC} = 10V, I _C = 2mA R _L = 100Ω	—	2	—	μs
Fall Time	t _f		—	3	—	
Turn-on Time	t _{on}		—	3	—	
Turn-off Time	t _{off}		—	3	—	
Turn-on Time	t _{ON}	R _L = 1.9kΩ (Fig.1)	—	2	—	μs
Storage Time	t _s	R _{BE} = OPEN V _{CC} = 5V, I _F = 16mA	—	15	—	
Turn-off Time	t _{OFF}	—	—	25	—	
Turn-on Time	t _{ON}	R _L = 1.9kΩ (Fig.1)	—	2	—	
Storage Time	t _s	R _{BE} = 220kΩ (TLP631) V _{CC} = 5V, I _F = 16mA	—	12	—	μs
Turn-off Time	t _{OFF}	—	—	20	—	

Fig.1 SWITCHING TIME TEST CIRCUIT

